

658

Patent Number(s): DE102010049658-A1; WO2012055574-A1

Title: System for generating and coherent detection terahertz radiation used in telecommunication application, has photosensitive active layer whose band edge wavelength is greater than wavelength the laser light source

Inventor Name(s): SARTORIUS B; ROEHLE H; STANZE D; DIETZ R

Patent Assignee(s): FRAUNHER GES FOERDERUNG ANGEWANDTEN EV (FRAU)

Derwent Primary Accession No.: 2012-E76108

Abstract: NOVELTY - The terahertz system has a laser light source (1) that is coupled with a transmitting antenna (2) and a receiving antenna (3) through an optical fiber (5). Each antenna has antenna conductors, photosensitive active layer and bordering layer. The band edge wavelength photosensitive active layer is 150 nm greater than wavelength the laser light source. The band edge wavelength bordering layer is smaller than the wavelength the laser light source.

USE - System for generating and coherent detection terahertz radiation used in telecommunication application.

ADVANTAGE - Since the band edge wavelength photosensitive active layer in antennas is greater than wavelength the laser light source, the transmitting efficiency transmitting antenna and receiving efficiency receiving antenna are improved. The coherent detection terahertz radiation can be performed easily with high precision.

DESCRIPTION DRAWING(S) - The drawing shows the schematic view the system for generating and coherent detection terahertz radiation.

Laser light source (1)

Transmitting antenna (2)

Receiving antenna (3)

Beam splitter (4)

Optical fiber (5)

Drawing:

Derwent Class Code(s): S03 (Scientific Instrumentation, photometry, calorimetry); V07 (Fibre-optics and Light Control); V08 (Lasers and Masers)

Derwent Manual Code(s): S03-E04A5; V07-F01A1; V08-A09

IPC: G01N-021/39; H01S-004/00; G01N-021/35

Patent Details:

Patent Number	Publ. Date	Main IPC	Week	Page Count	Language
DE102010049658-A1	26 Apr 2012	H01S-004/00	201232	Pages: 19	German
WO2012055574-A1	03 May 2012	G01N-021/35	201232		German

Application Details and Date:

DE102010049658-A1 DE10049658 25 Oct 2010

WO2012055574-A1 WOEP005530 25 Oct 2011

Priority Application Information and Date:

DE10049658 25 Oct 2010

Designated States:

WO2012055574-A1:

(National): AE; AG; AL; AM; AO; AT; AU; AZ; BA; BB; BG; BH; BR; BW; BY; BZ; CA; CH; CL; CN; CO; CR; CU; CZ; DE; DK; DM; DO; DZ; EC; EE; EG; ES; FI; GB; GD; GE; GH; GM;

GT; HN; HR; HU; ID; IL; IN; IS; JP; KE; KG; KM; KN; KP; KR; KZ; LA; LC; LK; LR; LS; LT; LU; LY; MA; MD; ME; MG; MK; MN; MW; MX; MY; MZ; NA; NG; NI; NO; NZ; OM; PE; PG; PH; PL; PT; QA; RO; RS; RU; RW; SC; SD; SE; SG; SK; SL; SM; ST; SV; SY; TH; TJ; TM; TN; TR; TT; TZ; UA; UG; US; UZ; VC; VN; ZA; ZM; ZW

Cited Patent(s):

DE102010049658-A1 DE102006010297-B3 BATOP GMBH (BATO-Non-standard)
HOHMUTH R; RICHTER W

DE102007012475-B4 FRAUNHER GES FOERDERUNG ANGEWANDTEN EV (FRAU)
SARTORIUS B; KUENZEL H; ROEHLE H; BIERMANN K

DE102007044839-A1 FRAUNHER GES FOERDERUNG ANGEWANDTEN EV (FRAU)
BACH H; ROEHLE H; SARTORIUS B

US2008279227-A1 NAT INST INFORMATION&COMMUNICATIONS TE (NICT)
NAKAYAMA M; MIZOGUCHI K; SAKAI K; SAITO S

WO2012055574-A1 DE102006010301-B3 BATOP GMBH (BATO-Non-standard)
HOHMUTH R; RICHTER W

DE102007044839-A1 FRAUNHER GES FOERDERUNG ANGEWANDTEN EV (FRAU)
BACH H; ROEHLE H; SARTORIUS B

FR2870386-A1 CNRS CENT NAT RECH SCI (CNRS); UNIV PARIS SUD
(UYPA-Non-standard) MANGENEY J; CROZART P; CHIMOT N; JOULAUD L; LOURTIOZ
J M

Cited Article(s):

DE102010049658-A1 "GaxIn1-xAs, Band structure and carrier concentration";
<http://www.ife.rssi.ru/SVA/NSM/Semicond/GaInAs/bandstr.html>, 24.10.2007

WO2012055574-A1 FRANCOEUR S ET AL: "Band gap GaAs1-xBix";
APPLIED PHYSICS LETTERS, AIP, AMERICAN INSTITUTE PHYSICS, MELVILLE, NY,
US, Bd. 82, Nr. 22, 2. Juni 2003 (2003-06-02), Seiten 3874-3876, XP012034254, ISSN:
0003-6951, DOI: 10.1063/1.1581983

PACEBUTAS V ET AL: "Terahertz time-domain-spectroscopy system based on
femtosecond Yb: fiber laser and GaBiAs photoconducting components";
APPLIED PHYSICS LETTERS, AIP, AMERICAN INSTITUTE PHYSICS, MELVILLE, NY, US, Bd. 97,
Nr. 3, 20. Juli 2010 (2010-07-20), Seiten 31111-31111, XP012138382, ISSN: 0003-6951, DOI:
10.1063/1.3458826

DYSON A ET AL: "Comparison Type I and Type II Heterojunction Untravelling Carrier
Photodiodes for Terahertz Generation"; IEEE JOURNAL SELECTED TOPICS IN
QUANTUM ELECTRONICS, IEEE SERVICE CENTER, PISCATAWAY, NJ, US, Bd. 14, Nr. 2,
1. M rz 2008 (2008-03-01), Seiten 277-283, XP011206852, ISSN: 1077-260X

STANZE D ET AL: "Coherent CW terahertz systems employing photodiode emitters";
INFRARED, MILLIMETER, AND TERAHERTZ WAVES, 2009. IRMMW-THZ 2009. 34TH
INTERNATIONAL CONFERENCE ON, IEEE, PISCATAWAY, NJ, USA, 21. September 2009
(2009-09-21), Seiten 1-3, XP031562560, ISBN: 978-1-4244-5416-7